

**Notice of References Cited**

Application/Control No.

09/927,694

Applicant(s)/Patent Under  
Reexamination  
BLACK ET AL.

Examiner

Maria Guerrero

Art Unit

2822

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,322,849	11-2001	Joshi et al.	427/96
	C	US-5,932,907	08-1999	Grill et al.	257/310
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Jung et al. "A Highly Reliable 1T/1C Ferroelectric Memory", 1998, IEEE, pages 122-123.
	V	Robert E. Jones, Jr. "Ferroelectric Nonvolatile Memories for Embedded Applications", 1998, IEEE, pages 431-438.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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